

# SILICON POWER TRANSISTOR 2SA1845

# PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1845 is a power transistor developed for high-speed switching and features a high here at low  $V_{CE(sat)}$ . This transistor is ideal for use as a driver in DC/DC converters and actuators.

In addition, this transistor features a package that can be auto-mounted in radial taping specifications, thus contributing to mounting cost reduction.

#### FEATURES

- Auto-mounting possible in radial taping specifications
- · Resin-molded insulation type package with power rating of 1.8 W in stand-alone conditions
- High hFE and low VCE(sat):

 $V_{CE(sat)} \le -0.3 \text{ V}$  @ Ic = -3.0 A, IB = -0.15 A

 $h_{FE} \geq 100 \qquad \qquad @V_{CE} = -2.0 \ V, \ I_C = -1.0 \ A$ 

· Fast switching speed

### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-150	V
Collector to emitter voltage	VCEO		-100	V
Emitter to base voltage	VEBO		-7.0	V
Collector current (DC)	IC(DC)		-5.0	А
Collector current (pulse)	C(pulse)	PW $\leq$ 300 $\mu$ s, duty cycle $\leq$ 2%	-10	А
Base current (DC)	B(DC)		-2.5	А
Total power dissipation	Ρτ	Ta = 25°C	1.8	w
Junction temperature	Tj		150	°C
Storage temperature	Tstg		-55 to +150	°C

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### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V <sub>CB</sub> = -100 V, I <sub>E</sub> = 0		-10	μA	
Collector cutoff current	ICER	V <sub>CE</sub> = -100 V, R <sub>EB</sub> = 50 Ω Ta = 125°C			-1.0	mA
Collector cutoff current	ICEX1	$V_{CE} = -100 \text{ V}, \text{ V}_{BE(off)} = 1.5 \text{ V}$			-10	μA
Collector cutoff current	ICEX2	$V_{CE} = -100 \text{ V}, V_{BE(off)} = 1.5 \text{ V}$ Ta = 125°C			-1.0	mA
Emitter cutoff current	Іево	$V_{EB} = -5.0 \text{ V}, \text{ Ic} = 0$			-10	μA
DC current gain	hfe1*	Vce = -2.0 V, Ic = -0.5 A	100			-
DC current gain	hFE2*	Vce = -2.0 V, Ic = -1.0 A	100		400	-
DC current gain	hfe3*	Vce = -2.0 V, Ic = -3.0 A	60			-
Collector saturation voltage	VCE(sat)1*	Ic = -3.0 A, Iв = -0.15 A			-0.3	V
Collector saturation voltage	VCE(sat)2*	Ic = -4.0 A, I <sub>B</sub> = -0.2 A			-0.5	V
Base saturation voltage	VBE(sat)1*	Ic = -3.0 A, Iв = -0.15 A			-1.2	V
Base saturation voltage	VBE(sat)2*	Ic = -4.0 A, I <sub>B</sub> = -0.2 A			-1.5	V
Gain bandwidth product	fт	Vce = -10 V, lc = -0.5 A		150		MHz
Collector capacitance	Cob	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$		130		pF
Turn-on time	ton	Ic = $-3.0$ A I <sub>B1</sub> = $-I_{B2}$ = $-0.15$ A R <sub>L</sub> = $16.7$ Ω, Vcc = $-50$ V			0.3	μs
Storage time	tstg				1.4	μs
Fall time	tr	$\Pi L = 10.7 \ \Sigma 2, \ V C C = -30 \ V$			0.4	μs

\* Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

#### **hfe CLASSIFICATION**

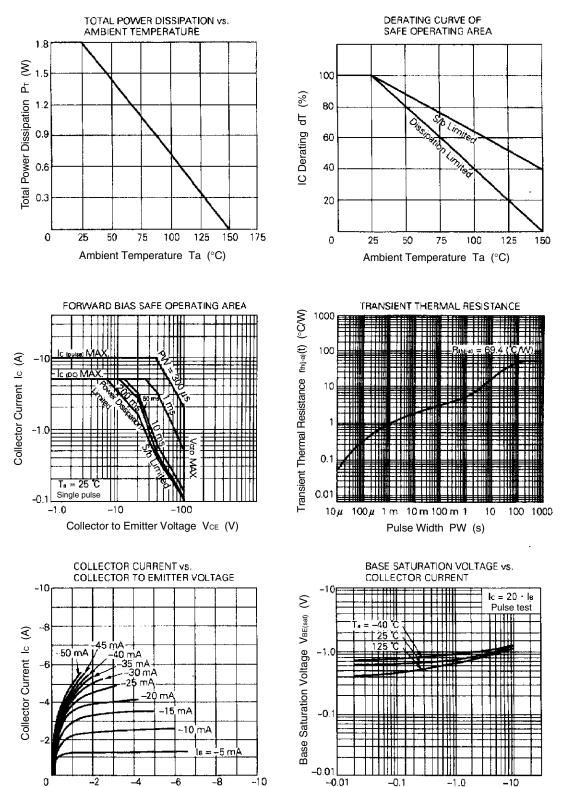
Marking	М	L	к	
hfe	100 to 200	150 to 300	200 to 400	

#### PACKAGE DRAWING (UNIT: mm) TAPING SPECIFICATION

#### $8.0 \pm 0.2$ A1 4.5 ± 0.2 А $13.0 \pm 0.2$ 0 0 8.0 o D٥ φ4.0 ± 0.2∙ d $0.5 \pm 0.1$ 0 0 2.5<sup>+0.4</sup> 2.5<sup>+0.4</sup> 2.5<sup>+0.4</sup> $13.0 \pm 0.2$ F٦ $F_2$ Н 20.0 MAX. Hα $16.0 \pm 0.5$ 32.2 MAX. Hı $2.5 \pm 0.2$ ⊿h 0 ± 1.0 2.5 MIN. l1 Р 12.7 ± 1.0 P٥ $12.7 \pm 0.3$ P $6.35 \pm 0.5$ 0.5 ± 0.1 đΡ $0 \pm 1.3$ $4.5 \pm 0.2$ ٣ W 18.0<sup>+1.0</sup> Lectrode Connection Po 5.0 MIN. Do Wo 1. Base W١ $9.0 \pm 0.5$ 2. Collector 0.7 MIN. W2 3. Emitter

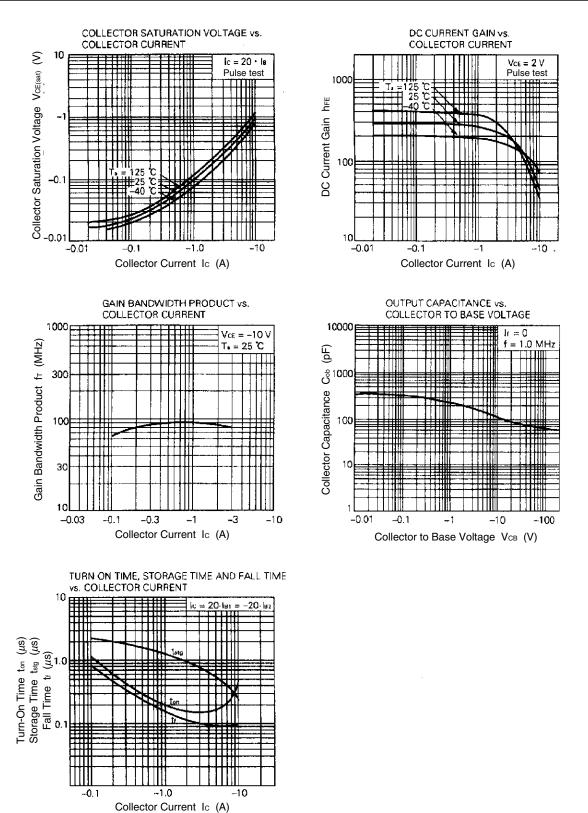
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#### **TYPICAL CHARACTERISTICS (Ta = 25°C)**

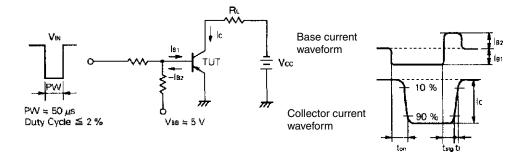


Collector Current Ic (A)

Collector to Emitter Voltage VCE (V)



## SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



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